

100mA 30V Low IR(0.21mm)

[Go to Home Page](#)

### Chip Information

Chip Size	0.21 x 0.21mm
Pad Size	0.138 x 0.138mm
Chip Quantity	251364 pcs/wafer
Scribe Line Width	40um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

### MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	0.5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-40 to +150	degC	

### ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.460	0.445	0.410	V	IF=10mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.3	0.2	0.015	uA	VR=10V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	30	33	50	V	IR=10uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

### Ordering Information

Chip Type	Chip Thickness	Back Metal
XFJ238	95 +/- 15um	Au(For Ag Epoxy)
XFJ239	100 +/- 15um	Au(For Eutectic)

Note:  
Designed For RB520ZS-30